

New Jersey Semi-Conductor Products, Inc.

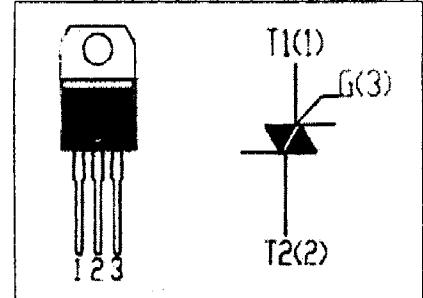
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BTB16-800SWRG

FEATURES

- With TO-220AB non insulated package
- Suitable for general purpose AC switching. Which can be used as an ON/OFF function in applications such as static relays, heating regulation.induction motor starting circuits. Or for phase control operation in light dimmers, motor speed controllers etc.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak off-state voltage	800	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_c=100^\circ C$	16	A
I_{TSM}	Non-repetitive peak on-state current $t_p=20ms$	160	A
T_j	Operating junction temperature	125	$^\circ C$
T_{stg}	Storage temperature	-40~150	$^\circ C$
$R_{th(j-c)}$	Thermal resistance, junction to case	1.2	$^\circ C/W$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	60	$^\circ C/W$

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ C$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $V_R=V_{RRM}, T_j=125^\circ C$	0.005 2	mA
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}$, $V_D=V_{DRM}, T_j=125^\circ C$	0.005 2	mA
I_{GT}	Gate trigger current	$V_D=12V; R_L=33\Omega$	10	mA
			10	
			10	
I_H	Holding current	$I_{GT}= 0.5A$, Gate Open	15	mA
V_{et}	Gate trigger voltage all quadrant	$V_D=12V; R_L=33\Omega$	1.3	V
V_{TM}	On-state voltage	$I_T= 22.5A; t_p= 380\mu s$	1.55	V



Quality Semi-Conductors